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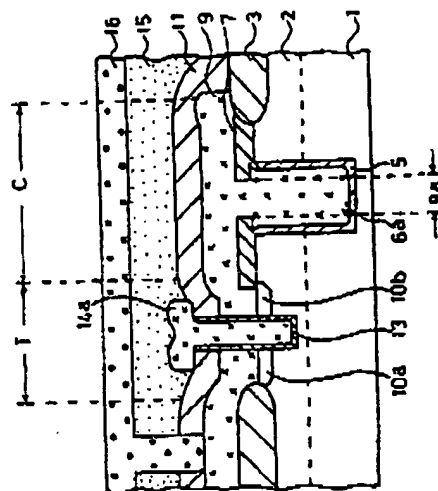
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APPLICATION NUMBER : 01008367

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TITLE : SEMICONDUCTOR STORAGE DEVICE  
AND MANUFACTURE THEREOF



**ABSTRACT :** PURPOSE: To connect a storage electrode of a storage capacitor to a drain electrode with good reproducibility and to simplify this connection process by a method wherein a transfer transistor and the storage capacitor are formed so as to be arranged in a transverse direction.

**CONSTITUTION:** In a semiconductor substrate 1, of one conductivity type, where a semiconductor layer 2 of an opposite conductivity type has been formed, the following are provided: a transfer transistor T composed of a source 10a and a drain 10b as one pair and of a word line 14a; and a storage capacitor C composed of a capacity insulating film 5 and a storage electrode 6a. Said transfer transistor T and said storage capacitor C are formed so as to be arranged in a transverse direction. A conductive film 9 connected to the source 10a or the drain 10b of the transfer transistor T is formed so as to be stretched on an element isolation film 7. The storage electrode 6a of said storage capacitor C is connected to said conductive film 9 via an opening part 8a which has been opened selectively in the element isolation film 7 on the storage electrode 6a.

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